IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony et al.

Docket:

TI-24953

Serial No.:

09/116,138

Examiner:

B. Souw

Filed:

07/15/98

Art Unit:

2814

1.3/1C 7-2500 C Bown



High Permittivity Silicate Gate Dielectric

REPLY PURSUANT TO 37 C.F.R. § 1.111

June 7, 2000

Assistant Commissioner for Patents Washington, DC 20231

Examiner:

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, DC 20231 on July 13, 2000.

David Denker Reg. No. 40,987

In response to the Office Action dated January 13, 2000, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please add Claims 41 - 45 as shown.

- 41. The method of Claim 1, where the metal silicate dielectric layer is a zirconium silicate dielectric layer.
- 42. The method of Claim 2, where the first metal is zirconium.
- 43. The method of Claim 16, where the first metal is zirconium.
- 44. The method of Claim\24, where the first metal is zirconium.
- 45. The method of Claim 28, where the metal silicate layer is a zirconium silicate layer.